Mar 31, 2021 **PCN Number:** 20210326002.1 **PCN Date:** Title: Qualification of MIHO8 as an additional Fab site option for select LBC8 devices Ouality Services **Customer Contact:** PCN Manager Dept: **Estimated Sample** Date provided at **Proposed 1st Ship Date:** Jun 30, 2021 **Availability:** sample request. **Change Type:** Assembly Materials Assembly Site **Assembly Process Electrical Specification** Mechanical Specification Design Packing/Shipping/Labeling Test Process Test Site Wafer Bump Site Wafer Bump Material Wafer Bump Process Wafer Fab Site Wafer Fab Materials Wafer Fab Process Part number change

### **Notification Details**

# **Description of Change:**

Texas Instruments is pleased to announce the qualification of its MIHO8 fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.

Cu	rrent Fab Sit	e	Additional Fab Site			
Current Fab Site			New Fab Site	Process	Wafer Diameter	
DP1DM5	LBC8	200mm	MIHO8	LBC8	200mm	

Qual details are provided in the Qual Data Section.

# **Reason for Change:**

Continuity of supply.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

None

# Changes to product identification resulting from this PCN:

# **Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas
MIHO8	MH8	JPN	Ibaraki

Sample product shipping label (not actual product label)

TEXAS
INSTRUMENTS
MADE IN: Malaysia
2DC: 20:
MSL '2 /260C/1 YEAR SEAL DT

MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: 39

LBL: 5A (L)T0:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$I2 (P) (2P) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO: USA

### **Product Affected:**

LMR23610ADDA	LMR23625CFDDA	LMR23630AFDDA	LMR23630FDRRR
LMR23610ADDAR	LMR23625CFDDAR	LMR23630AFDDAR	LMR23630FDRRT
LMR23615DRRR	LMR23625CFPDRRR	LMR23630APDRRR	LMZM33602RLRR
LMR23615DRRT	LMR23625CFPDRRT	LMR23630APDRRT	LMZM33603RLRR
LMR23625CDDA	LMR23630ADDA	LMR23630DRRR	

	LMR23625CDDAR	LMR23630ADDAR	LMR23630DRRT
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# Automotive New Product Qualification Summary (As per AEC-Q100, Q006 and JEDEC Guidelines)

# Approved 11-20-2019

### Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as: Number of lots / Total sample size / Total failed									
Тур	e #	Test Spec	Min Lot Qty	:	SS/Lot	Те	Test Name / Condition		Qual Device LMR23630xQDRRQ1	QBS Process Reference: LM46002AQPWPRQ1
			Te	st Group	A – Accelera	ted Environme	ent Stress Tests			
PC	A1	JEDEC J- STD-020 JESD22- A113	3	All unit	s for A2 to A5		MSL2/260C	-	3/693/0 for A2 to A4 1/45/0 for A5	-
HAS	T A2	JEDEC JESD22- A110	3		77	Biase	ed HAST, 130C/85%RH	96 hours	3/231/0	-
AC	А3	JEDEC JESD22- A102	3		77		Autoclave 121C	96 hours	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3		77	Temp	erature Cycle, -65/150C	500 cycles	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	1		5 units	Temp	erature Cycle, -65/150C	Post 500 cycles	5 units/ 30 wires pass.	-
PTC	A5	JEDEC JESD22- A105	1		45	Power Te	emperature Cycle, -40/125C	1000 cycles	1/45/0	-
HTS	L A6	JEDEC JESD22- A103	1		45	High T	High Temp Storage Bake 150C		1/45/0	-
			т.		- D. Assalan	-4     :5-4: (	Ninnaletia a Tanta			
			JED		D B - Acceler	ated Lifetime :	Simulation Tests			
	HTOL	B1	JESI A1	022- 08	1	77	Life Test, 125C	1000 hours	3/231/0	-
	ELFR	B2	Q100	)-008	1	800	Early Life Failure Rate, 150C	24 hours	QBS	3/2400/0
	EDR	B3	Q100	-005		77	NVM Endurance, Data Retention, 150C Integrity Tests	1000 hours	QBS	3/231/0
			AE	C						-
	WBS	C1	Q100 MI	)-001 1		30	Wire Bond Shear (Cpk>1.67)	-	1/30/0	-
	WBP	C2	STD Meti 20	nod <sup>1</sup>		30	Wire Bond Pull (Cpk>1.67)	-	1/30/0	
	SD	C3	JED JESI B1	022- 1 02		15	Surface Mount Solderability >95% Lead Coverage	-	1/15/0	-
	PD	C4	JED JESI B100 B1	022- and 08		10	Physical Dimensions (Cpk>1.67)	-	3/30/0	-
			D – Die	Fabricat	ion Reliabilit	Tests				
EM	D1	JESD61	-	-		migration Dependent				echnology Requirements
TDDB	D2	JESD35 JESD60 &	-	-	Dielectric	Breakdown				echnology Requirements
HCI	D3	28	-	-		tive Bias			Completed Per Process 1	echnology Requirements
NBTI	D4	-	-	.   -	_	ure Instability			Completed Per Process Technology Requirements	

Stress Migration

Completed Per Process Technology Requirements

		1						
НВМ	E2	AEC Q100-002	1	3	ESD - HBM - Q100 2000 Volts		1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	750 volts	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-up	125C	1/3/0	-
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0	-

<sup>-</sup> QBS: Qual By Similarity

A1 (PC): Preconditioning:
Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

### Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

### Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

# Automotive Product change Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

# Approved 26-Dec-2019

### **Qualification Results** Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMR236xxQDDA	QBS Wafer fab Process Reference: <u>LM4360xxQPWPRQ1</u>	QBS Package Reference: <u>LMR236xxQDDAQ1</u>
			Test Group	A – Acce						
	PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning Level 2	260C	QBS	3/693/0	3/693/0
	ТНВ	A2	JEDEC JESD22- A101	3	77	Biased Temperature and Humidity, 85C/85%RH	1000 hours	QBS	3/231/0	3/231/0
	AC	A3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 hours	QBS	3/231/0	3/231/0
	тс	Α4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 cycles	QBS	3/231/0	3/231/0
	TC	Α4	Post Temp cycle bond pulls	1	5 units	Post-500 cycles	-	QBS	1/5/0	1/5/0
	PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, - 40/125C	1000 cycles	QBS	1/45/0	1/45/0
	HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 150C	1000 hours	QBS	3/231/0	3/231/0
			Test Group	B – Acce	elerated L	ifetime Simulation Tests		Note 2		
ı	HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 150C	408 hours	QBS	3/231/0	-
-	ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 hours	QBS	3/2400/0	-
	EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	1000 hours	QBS	3/231/0	-
			Test Gro	up C – Pa	ickage As	sembly Integrity Tests				
	WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	-	QBS	-	1/30/0

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMR236xxQDDA	QBS Wafer fab Process Reference: LM4360xxQPWPRQ1	QBS Package Reference: <u>LMR236xxQDDAQ1</u>
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	-	QBS	-	1/30/0
SD	СЗ	JEDEC JESD22- B102	1	15	Auto Solderability (Pb and Pb- Free)	>95% Lead Coverage	QBS	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.33 Ppk>1.67	QBS	-	3/30/0
		Test Gr	oup D – D	ie Fabrica	ation Reliability Tests				
EM	D1	JESD61	-	-	Electro-migration	-	Completed P	-	
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	R	Completed Per Process Technology Requirements	
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-		Completed Per Process Technology Requirements	
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	R	Completed Per Process Technology Requirements	
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements		-
		Test	Group E -	- Electrica	l Verification Tests				
НВМ	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	-	
CDM	E3	AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	-	
LU	E4	AEC Q100-004	1	6	Latch-up	125C	1/6/0	-	
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/30/0	-	

<sup>-</sup> QBS: Qual By Similarity

Note 1: Top metallization of the silicon die is the same process and same factory location for both primary and second sourced fab products – supports QBS for group A and group C tests.

Note 2: Silicon IP components of the LMR232xxQDDA are used in LM4360xxQPWPRQ1

### A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable

Ambient Operating Temperature by Automotive Grade Level: Grade 1 (or Q): -40°C to +125°C E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL, ED

Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

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<sup>-</sup> Qual Device LMR236xxQDDARQ1 is qualified at LEVEL2-260CG

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